

INCHANGE SEMICONDUCTOR

isc Silicon NPN Power Transistor

BUW11A

DESCRIPTION

- High Voltage
- High Speed Switching
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

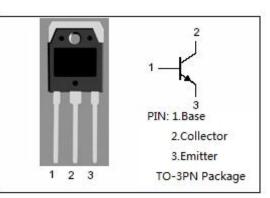
- Converters
- Inverters
- · Switching regulators
- Motor control systems

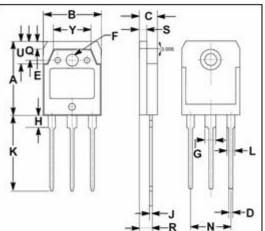
ABSOLUTE MAXIMUM RATINGS (Ta=25℃)

PARAMETER	VALUE	UNIT	
Collector-Base Voltage	1000	v	
Collector-Emitter Voltage	450	V	
Emitter-Base Voltage	9	V	
Collector Current-Continuous	5	A	
Collector Current-Peak	10	А	
Base Current	2	А	
Base Current-Peak	4	A	
Collector Power Dissipation $@T_c=25^{\circ}C$	100	W	
Junction Temperature	150		
Storage Temperature Range	-65~150	°C	
	Collector-Base Voltage Collector-Emitter Voltage Emitter-Base Voltage Collector Current-Continuous Collector Current-Peak Base Current Base Current-Peak Collector Power Dissipation @Tc=25°C Junction Temperature	Collector-Base Voltage1000Collector-Emitter Voltage450Emitter-Base Voltage9Collector Current-Continuous5Collector Current-Peak10Base Current2Base Current-Peak4Collector Power Dissipation @Tc=25°C100Junction Temperature150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT
Rth j-c	Thermal Resistance, Junction to Case	1.25	°C/W





	m	m
DIM	MIN	MAX
Α	19.60	20.30
В	15.50	15.70
С	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
Н	3.20	3.40
J	0.595	0.605
K	19.80	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.20
Y	9.90	10.10

isc website: www.iscsemi.com



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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР.	МАХ	UNIT
Vceo(sus)	Collector-Emitter Sustaining Voltage	I _C = 50mA; I _B = 0	450			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 2.5A; I _B = 0.5A			1.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = 2.5A; I _B = 0.5A			1.4	V
I _{CES}	Collector Cutoff Current	V _{CE} =RatedV _{CES} ;V _{BE} = 0 V _{CE} =RatedV _{CES} ;V _{BE} = 0;T _C =125°C			1 2	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 9V; I _C = 0			10	mA
hfe-1	DC Current Gain	Ic= 5mA ; Vce= 5V	10		35	
h _{FE-2}	DC Current Gain	I _C = 0.5A ; V _{CE} = 5V	10		35	

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